

In the Specification:

Please replace the paragraph beginning at page 14, line 12, with the following rewritten paragraph:

C²

-- After the ion implantation step, the deposits 4 made on the face 5 of the substrate 1 are removed. The face 5 of the substrate 1 can be made integral with a receiving surface of a support 3 by molecular adhesion (see Figure 3). Before this integration step, the faces to be joined are prepared in order to constitute a bonding interface. By way of example, an ohmic contact of very low resistivity ($1 \Omega \cdot \text{cm}$) can be obtained if the bonding is carried out using an intermediate layer of palladium 10 deposited on one of the faces or on both the faces to be joined. A similar result can be obtained in the case of a brazing material, such as an indium based brazing material.--